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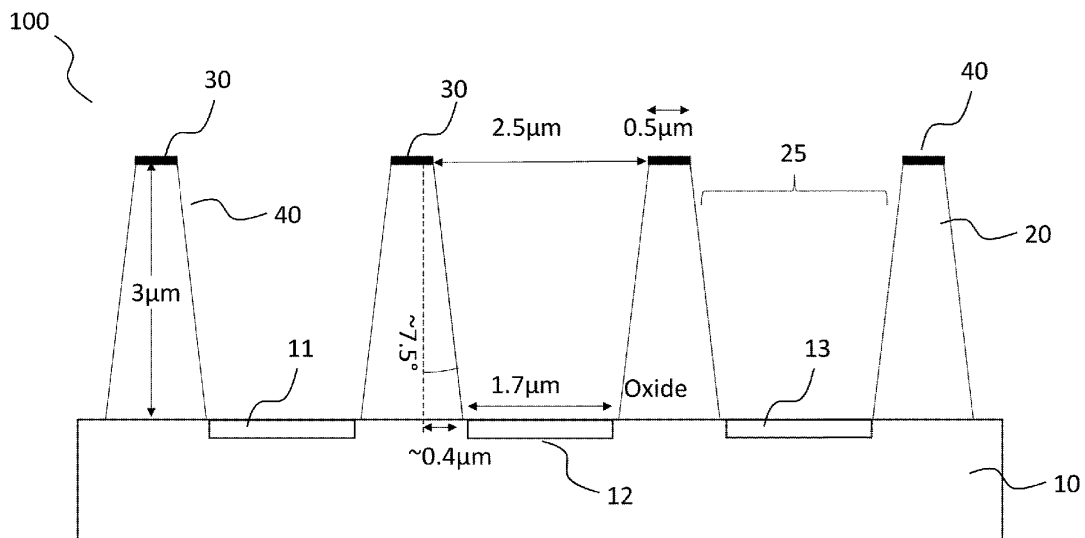


Figure 1

(57) Abstract: A method of manufacturing a light emitting diode array comprising a first layer having a plurality of light emitting diodes arranged to emit light from a light emitting surface of the first layer, the method comprising: depositing a layer of dielectric material over the light emitting surface of the first layer; forming a plurality of apertures extending through the layer of dielectric material, each aperture having an internal surface that is at least partially reflective, wherein at least one aperture of the plurality of apertures is centered on and aligned with a light emitting diode of the plurality of light emitting diodes of the first layer, such that light emitted from light emitting diode is collimated as it passes through the at least one aperture.

[Continued on next page]

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